

*New Jersey Semi-Conductor Products, Inc.*

20 STERN AVE.  
SPRINGFIELD, NEW JERSEY 07081  
U.S.A.

**2N/PN/SST4391**

**SERIES**

**SINGLE N-CHANNEL JFET SWITCH**

**FEATURES**

Replacement for Siliconix 2N/PN/SST4391, 4292, & 4393

LOW ON RESISTANCE	$r_{DS(on)} \leq 30\Omega$
-------------------	----------------------------

FAST SWITCHING	$t_{ON} \leq 15\text{ns}$
----------------	---------------------------

**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>**

@ 25 °C (unless otherwise stated)

**Maximum Temperatures**

Storage Temperature (2N)	-65 to 200°C
--------------------------	--------------

Storage Temperature (PN/SST)	-55 to 150°C
------------------------------	--------------

Junction Operating Temperature (2N)	-55 to 200°C
-------------------------------------	--------------

Junction Operating Temperature (PN/SST)	-55 to 150°C
---	--------------

**Maximum Power Dissipation**

Continuous Power Dissipation (2N)@ $T_c=25^\circ\text{C}$	1800mW <sup>3</sup>
---	---------------------

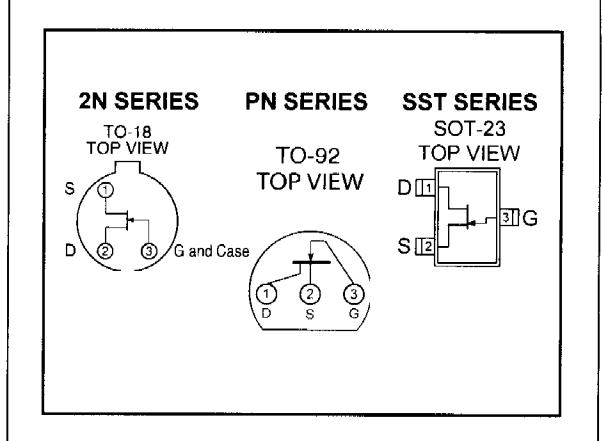
Continuous Power Dissipation (PN/SST)	350mW <sup>4</sup>
---------------------------------------	--------------------

**Maximum Currents**

Gate Current	50mA
--------------	------

**Maximum Voltages**

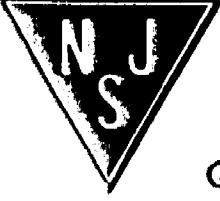
Gate to Drain or Source (2N/PN)	-40V
---------------------------------	------



**STATIC ELECTRICAL CHARACTERISTICS @25 °C (unless otherwise stated)**

SYM.	CHARACTERISTIC	TYP	4391		4392		4393		UNIT	CONDITIONS
			MIN	MAX	MIN	MAX	MIN	MAX		
BV <sub>GSS</sub>	Gate to Source Breakdown Voltage	2N/PN/SST	-40		-40		-40			
V <sub>GS(off)</sub>	Gate to Source Cutoff Voltage	2N/PN	-4	-10	-2	-5	-0.5	-3		
V <sub>GS(F)</sub>	Gate to Source Forward Voltage	0.7		1		1		1	V	
V <sub>DS(on)</sub>	Drain to Source On Voltage	0.25						0.4		
		0.3				0.4				
		0.35		0.4						
I <sub>DS</sub>	Drain to Source Saturation Current <sup>2</sup>	2N	50	165	25	150	5	125		
		PN	50	165	25	150	5	125	mA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
		SST	50		25		5			V <sub>DS</sub> = 15V, I <sub>D</sub> = 10nA
I <sub>GSS</sub>	Gate Leakage Current	2N/SST	-5		-100		-100			I <sub>G</sub> = -1μA, V <sub>DS</sub> = 0V
		PN	-5		-1000		-1000		pA	V <sub>GS</sub> = -20V, V <sub>DS</sub> = 0V
I <sub>G</sub>	Gate Operating Current	-5								V <sub>DG</sub> = 15V, I <sub>D</sub> = 10mA

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

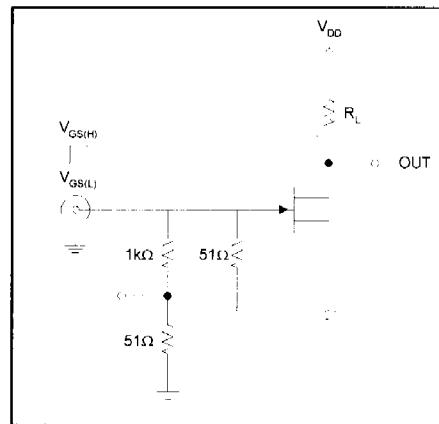




### SWITCHING CIRCUIT CHARACTERISTICS

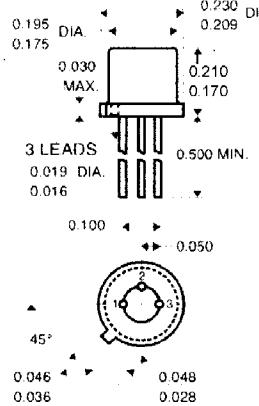
SYM.	4391	4392	4393
$V_{GS(L)}$	-12V	-7V	-5V
$R_L$	800Ω	1600Ω	3200Ω
$I_{D(on)}$	12mA	6mA	3mA

### SWITCHING TEST CIRCUIT

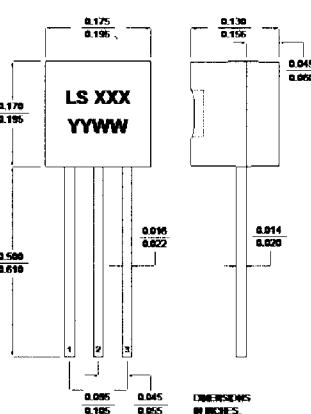


TO-18 \*

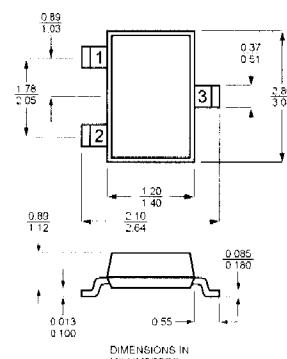
Three Lead



TO-92 \*



SOT-23



\*Dimensions in inches